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## PATENT APPLICATION

45-9000 m

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE 1970

In re the Application of

Teruo TAKIZAWA, Hiroyuki SHIMADA

Application No.: U.S. National Stage

of PCT/JP00/03968

Filed: February 21, 2001

Docket No.: 108680

For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

## PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

## IN THE CLAIMS:

Please replace claim 3 as follows:

3. (Amended) A semiconductor device according to claim 1, wherein p-type impurities are doped into said germanium film.

Please add new claim 14 as follows:

-- 14. A semiconductor device according to claim 2, wherein p-type impurities are doped into said germanium film. --